

Thyristor sensitive gate

2N5064

GENERAL DESCRIPTION

Glass passivated sensitive gate thyristor in a plastic envelope, intended for use in general purpose switching and phase control applications. This device is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

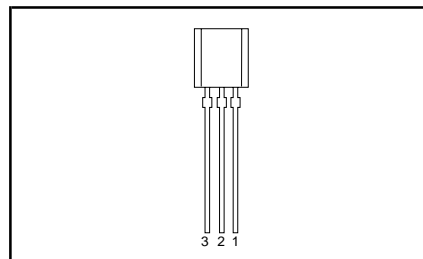
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages	200	V
$I_{T(AV)}$	Average on-state current	0.5	A
$I_{T(RMS)}$	RMS on-state current	0.8	A
I_{TSM}	Non-repetitive peak on-state current	10	A

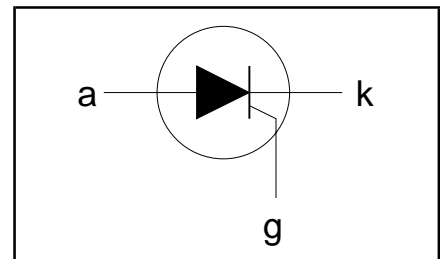
PINNING - TO92 variant

PIN	DESCRIPTION
1	anode
2	gate
3	cathode

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages		-	200	V
$I_{T(AV)}$	Average on-state current	half sine wave $T_c \leq 67^\circ\text{C}$	-	0.51	A
$I_{T(RMS)}$	RMS on-state current	$T_c \leq 102^\circ\text{C}$	-	0.255	A
I_{TRM}	Repetitive peak on-state current	all conduction angles	-	0.8	A
I_{TSM}	Non-repetitive peak on-state current		-	8	A
I^2t	I^2t for fusing	half sine wave; $T_a = 25^\circ\text{C}$ prior to surge; $t = 8.3\text{ ms}$	-	10	A
I_{GM}	Peak gate current		-	0.4	A^2s
V_{GM}	Peak gate voltage	$T_a = 25^\circ\text{C}, t_p = 300\mu\text{s}; f = 120\text{ Hz}$	-	1	A
V_{RGM}	Peak reverse gate voltage		-	5	V
P_{GM}	Peak gate power		-	5	V
$P_{G(AV)}$	Average gate power	$T_a = 25^\circ\text{C}$	-	0.1	W
T_{stg}	Storage temperature	$T_a = 25^\circ\text{C}, \text{ over any } 16\text{ ms period}$	-	0.01	W
T_j	Operating junction temperature		-65	150	$^\circ\text{C}$
			-65	125	$^\circ\text{C}$

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	see note: ¹	-	-	75	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		-	200	-	K/W

STATIC CHARACTERISTICS
 $T_c = 25\text{ }^\circ\text{C}$, $R_{GK} = 1\text{ k}\Omega$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	$T_c = 25\text{ }^\circ\text{C}$ $T_c = -65\text{ }^\circ\text{C}$ $V_D = V_{DRM(max)}$; $R_L = 100\ \Omega$; gate open circuit	-	-	200 350	μA μA
I_L	Latching current	$V_D = 12\text{ V}$; $R_{GK} = 1\text{ k}\Omega$	-	-	6	mA
I_H	Holding current	$V_D = 12\text{ V}$; $R_{GK} = 1\text{ k}\Omega$	-	-	5	mA
V_T	On-state voltage	$I_T = 1.2\text{ A peak}$; $t_p = 300\ \mu\text{s}$; $\delta \leq 0.01$	-	-	1.7	V
V_{GT}	Gate trigger voltage	$T_j = 25\text{ }^\circ\text{C}$ $T_j = -65\text{ }^\circ\text{C}$ $T_j = 125\text{ }^\circ\text{C}$ $V_D = V_{DRM(max)}$; $R_L = 100\ \Omega$; gate open circuit	-	-	0.8 1.2 -	V V V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}$; $V_R = V_{RRM(max)}$ $T_j = 25\text{ }^\circ\text{C}$ $T_j = 125\text{ }^\circ\text{C}$	-	-	10 50	μA μA

DYNAMIC CHARACTERISTICS
 $T_c = 25\text{ }^\circ\text{C}$, $R_{GK} = 1\text{ k}\Omega$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; $R_{GK} = 1\text{ k}\Omega$	-	25	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 2\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 10\text{ mA}$; $dI_G/dt = 0.1\text{ A}/\mu\text{s}$	-	2	-	μs
t_q	Circuit commutated turn-off time	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{TM} = 1.6\text{ A}$; $V_R = 35\text{ V}$; $dI_{TM}/dt = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 2\text{ V}/\mu\text{s}$; $R_{GK} = 1\text{ k}\Omega$	-	100	-	μs

¹ This measurement is made with the case mounted "flat side down" on a heatsink and held in position by means of a metal clamp over the curved surface.

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MECHANICAL DATA

Dimensions in mm

Net Mass: 0.2 g

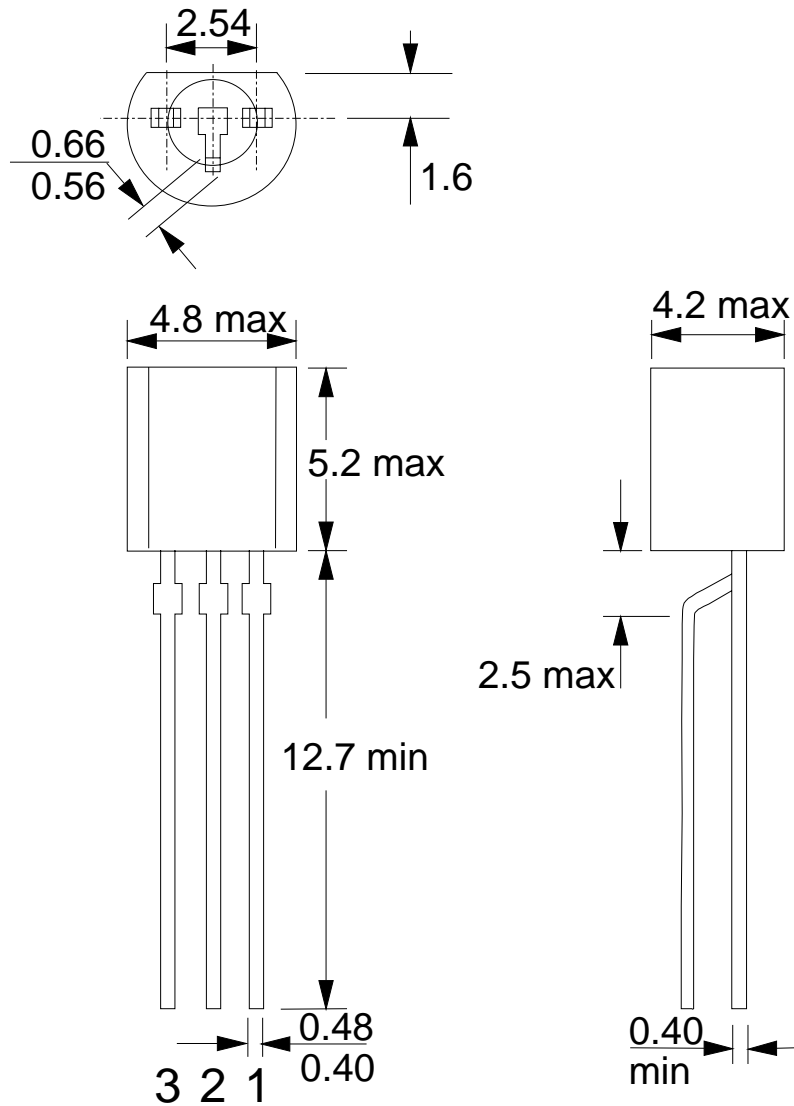


Fig.1. TO92; plastic envelope.

Notes

1. Epoxy meets UL94 V0 at 1/8".